Amendments to the Specification

Paragraph at page 1, lines 6, 7:

This application is a division of Serial No. 10/096,168, filed March 12, 2002, ~~issue fee paid~~ now issued as US Patent 6,743,425.

Paragraph at page 3, line 3-11:

A wafer 22 to be sputter coated is supported on a temperature controlled pedestal electrode 24. The wafer 22 may be secured to the pedestal electrode 24 by a clamp ring 26, but an electrostatic chuck may alternatively be used. A grounded shield 28 supported on the sidewalls 12 protects the chamber walls and sides of the pedestal 24 from being coated with sputtered material and further acts as ~~a cathode~~ an anode for the diode sputtering process. The argon working gas is admitted into a processing space 30 over the wafer 22 through gaps between the pedestal 24, the wafer clamp 26, and the grounded shield 28. The high density plasma being generated benefits from an electrically floating shield 32 supported on the grounded shield 28 through an isolator 34.

Paragraph at page 10, lines 25-28:

A flange 176 extending radially outwardly from the bottom of the sidewall 166 may be used to support the target 162 on the chamber body. However, [[the]] the throat ring 172 may be used for the same purpose. The relative axial positions of the throat ring 172 and flange 176 may be varied.